

20A, 150V N-CHANNEL POWER MOSFET

■ DESCRIPTION

The UTC **20N15** is an N-Channel POWER MOSFET, it uses UTC's advanced technology to provide customers with high switching speed and low gate charge.

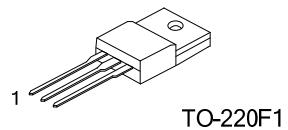
The UTC **20N15** is suitable for bridge circuits, power converters and PWM motor controls.

■ FEATURES

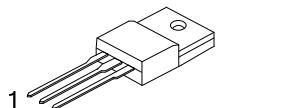
* $R_{DS(on)} < 0.13\Omega$ @ $V_{GS} = 10V$, $I_D = 10A$

* High switching speed

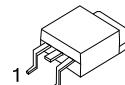
* Low gate charge



TO-220F1

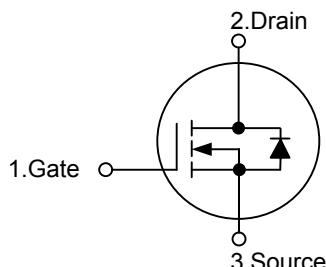


TO-220F2



TO-252

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
20N15L-TF1-T	20N15G-TF1-T	TO-220F1	G	D	S	Tube
20N15L-TF2-T	20N15G-TF2-T	TO-220F2	G	D	S	Tube
20N15L-TN3-T	20N15G-TN3-T	TO-252	G	D	S	Tube
20N15L-TN3-R	20N15G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

20N15L-TF1-T  (1)Packing Type (2)Package Type (3)Lead Free	(1) T: Tube, R: Tape Reel (2) TF1: TO-220F1, TF2: TO-220F2, TN3: TO-252 (3) L: Lead Free, G: Halogen Free
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■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	150	V
Gate-Source Voltage	Continuous	V_{GSS}	± 20	V
Drain Current	Continuous	I_D	20	A
	Single Pulsed ($t_p \leq 10\mu\text{s}$)	I_{DM}	60	A
Single Drain-to-Source Avalanche Energy	Starting $T_J=25^\circ\text{C}$ ($V_{DD}=120\text{V}$, $V_{GS}=10\text{V}$, $I_L=20\text{A}$, $L=0.3\text{mH}$)	E_{AS}	60	mJ
Power Dissipation	TO-220F1	P_D	36	W
	TO-220F2		38	W
	TO-252		50	W
Operating Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-55~+150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F1/TO-220F2	θ_{JA}	62.5	$^\circ\text{C/W}$
	TO-252		110	$^\circ\text{C/W}$
Junction to Case	TO-220F1	θ_{JC}	3.47	$^\circ\text{C/W}$
	TO-220F2		3.28	$^\circ\text{C/W}$
	TO-252		2.5	$^\circ\text{C/W}$

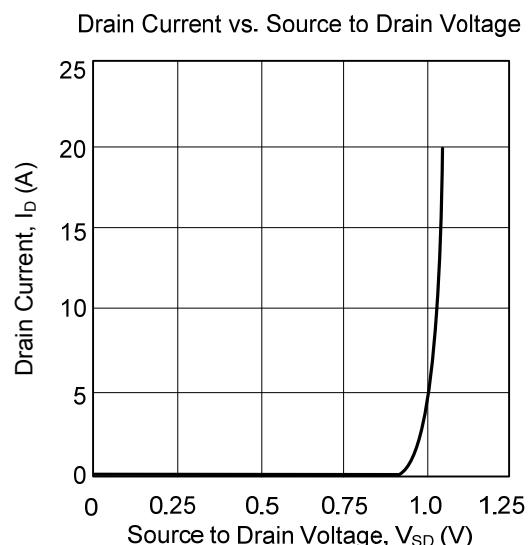
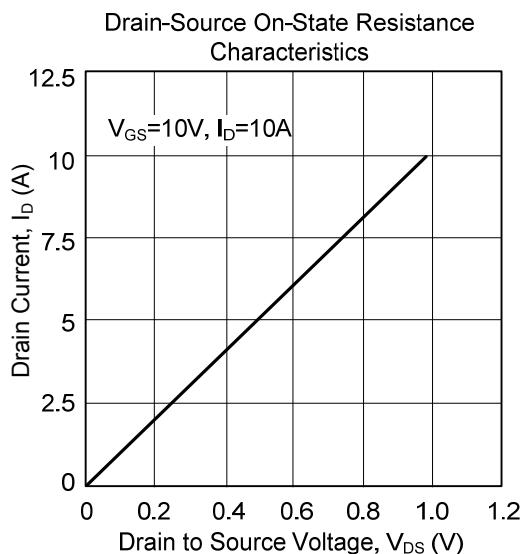
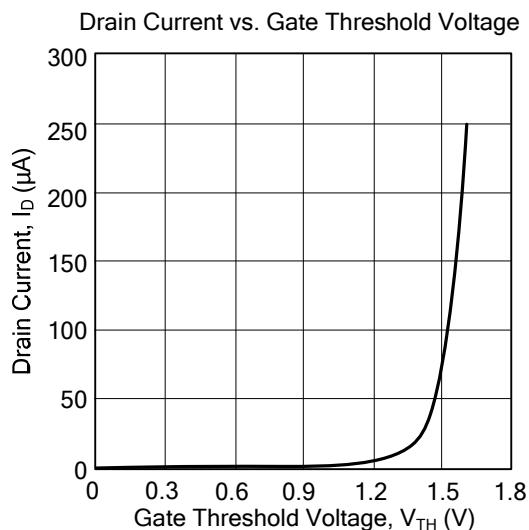
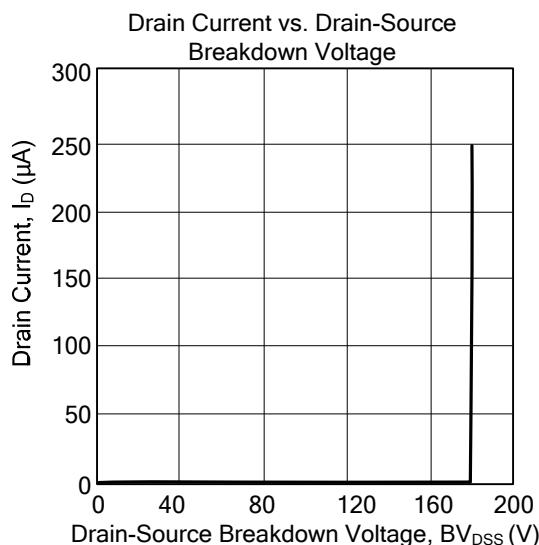
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=0.25\text{mA}, V_{GS}=0\text{V}$	150			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=150\text{V}, V_{GS}=0\text{V}$		10		μA
		$V_{DS}=150\text{V}, V_{GS}=0\text{V}, T_J=125^\circ\text{C}$		100		μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=+20\text{V}, V_{DS}=0\text{V}$		100		nA
		$V_{GS}=-20\text{V}, V_{DS}=0\text{V}$		100		nA
ON CHARACTERISTICS (Note 1)						
Gate Threshold Voltage	$V_{GS(\text{TH})}$	$V_{DS}=V_{GS}, I_D=0.25\text{mA}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{GS}=10\text{V}, I_D=10\text{A}$		0.12	0.13	Ω
Drain-Source On-Voltage	$V_{\text{DS(ON)}}$	$V_{GS}=10\text{V}, I_D=20\text{A}$			2.8	V
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}, V_{DS}=25\text{V}, f=1.0\text{MHz}$		1133	1627	pF
Output Capacitance	C_{OSS}			332	474	pF
Reverse Transfer Capacitance	C_{RSS}			105	174	pF
SWITCHING PARAMETERS (Note 2)						
Gate Charge	Q_G	$V_{GS}=10\text{V}, V_{DS}=75\text{V}, I_D=20\text{A}$		39.1	55.9	nC
	Q_{GS}			7.5		nC
	Q_{GD}			22		nC
Turn-ON Delay Time	$t_{D(\text{ON})}$	$V_{DD}=75\text{V}, V_{GS}=10\text{V}, I_D=20\text{A}, R_G=9.1\Omega$		11	25	ns
Rise Time	t_R			77	153	ns
Turn-OFF Delay Time	$t_{D(\text{OFF})}$			33	67	ns
Fall-Time	t_F			49	97	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=20\text{A}, V_{GS}=0\text{V}$			1.5	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				20	A
Pulsed Drain-Source Current	I_{SM}				60	A
Body Diode Reverse Recovery Time	t_{RR}	$I_S=20\text{A}, V_{GS}=0\text{V}, dI_S/dt=100\text{A}/\mu\text{s}$		160		ns
Body Diode Reverse Recovery Charge	Q_{RR}			1.1		μC

Notes: 1. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%.

2. Switching characteristics are independent of operating junction temperature.

- TYPICAL CHARACTERISTICS



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